

单 P 沟道 MOSFET

ELM57317WSA-N

<http://www.elm-tech.com>

■概要

ELM57317WSA-N 是 P 沟道低输入电容，低工作电压，低导通电阻的大电流 MOSFET。

■特点

- $V_{ds} = -150V$
- $I_d = -3.0A$
- $R_{ds(on)} = 750m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} = 800m\Omega$ ($V_{gs} = -6V$)

■绝对最大额定值

如没有特别注明时, $T_a = 25^\circ C$

项目	记号	规格范围	单位
漏极 - 源极电压	V_{ds}	-150	V
栅极 - 源极电压	V_{gs}	± 20	V
漏极电流 (定常) $T_j = 150^\circ C$	I_d	$T_a = 25^\circ C$	-3.0
		$T_a = 70^\circ C$	-2.4
漏极电流 (脉冲)	I_{dm}	-2	A
容许功耗	P_d	$T_c = 25^\circ C$	28
		$T_c = 70^\circ C$	18
动作结合部温度	T_j	150	$^\circ C$
保存温度范围	T_{stg}	-55 ~ 150	$^\circ C$

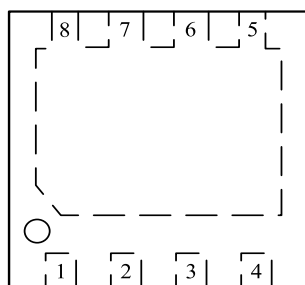
■热特性

项目	记号	典型值	最大值	单位
最大结合部 - 环境热阻	$R_{\theta ja}$		120	$^\circ C/W$

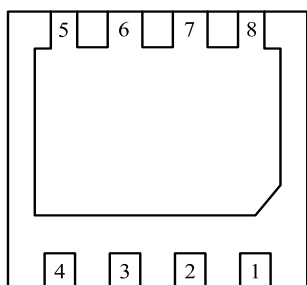
■引脚配置图

DFN8-3 × 3

(俯视图)

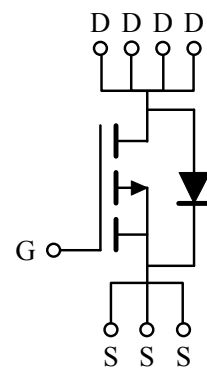


(背面视图)



引脚编号	引脚名称
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■电路图



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■电特性

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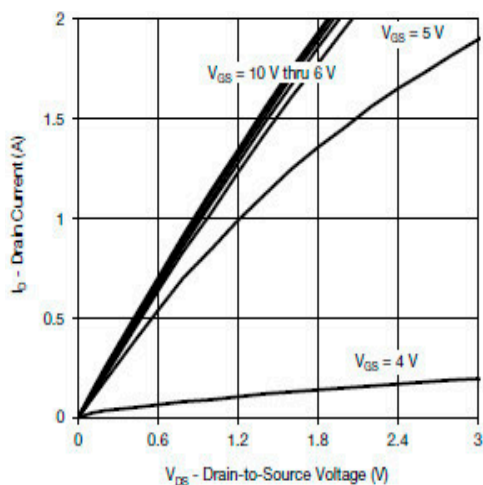
项目	记号	条件	最小值	典型值	最大值	单位
静态特性						
漏极 - 源极击穿电压	BV _{dss}	$I_d=-250\mu\text{A}, V_{gs}=0\text{V}$	-150			V
栅极接地时漏极电流	I _{dss}	$V_{ds}=-120\text{V}$			-1	μA
		$V_{gs}=0\text{V}$		$T_a=85^\circ\text{C}$	-30	
栅极漏电流	I _{gss}	$V_{ds}=0\text{V}, V_{gs}=\pm 20\text{V}$			± 100	nA
栅极阈值电压	V _{gs(th)}	$V_{ds}=V_{gs}, I_d=-250\mu\text{A}$	-2.0		-4.0	V
导通时漏极电流	I _{d(on)}	$V_{gs}=-10\text{V}, V_{ds}\geq -15\text{V}$	-1.6			A
漏极 - 源极导通电阻	R _{ds(on)}	$V_{gs}=-10\text{V}, I_d=-1.4\text{A}$		675	750	m Ω
		$V_{gs}=-6\text{V}, I_d=-1.0\text{A}$		720	800	
正向跨导	G _{fs}	$V_{ds}=-15\text{V}, I_d=-0.5\text{A}$		3		S
二极管正向压降	V _{sd}	$I_s=-1.0\text{A}, V_{gs}=0\text{V}$		-0.75	-1.20	V
寄生二极管最大连续电流	I _s				-2.7	A
动态特性						
输入电容	C _{iss}	$V_{gs}=0\text{V}, V_{ds}=-75\text{V}, f=1\text{MHz}$		280		pF
输出电容	C _{oss}			20		pF
反馈电容	C _{rss}			15		pF
开关特性						
总栅极电荷	Q _g	$V_{gs}=-10\text{V}, V_{ds}=-75\text{V}$ $I_d\equiv -1.1\text{A}$		8.0	15.0	nC
栅极 - 源极电荷	Q _{gs}			2.0		nC
栅极 - 漏极电荷	Q _{gd}			2.5		nC
导通延迟时间	t _{d(on)}	$V_{gs}=-10\text{V}, V_{ds}=-75\text{V}$ $R_L=85\Omega, I_d\equiv -1.0\text{A}$ $R_{gen}=1.0\Omega$		10	20	ns
导通上升时间	t _r			15	30	ns
关闭延迟时间	t _{d(off)}			15	30	ns
关闭下降时间	t _f			10	25	ns

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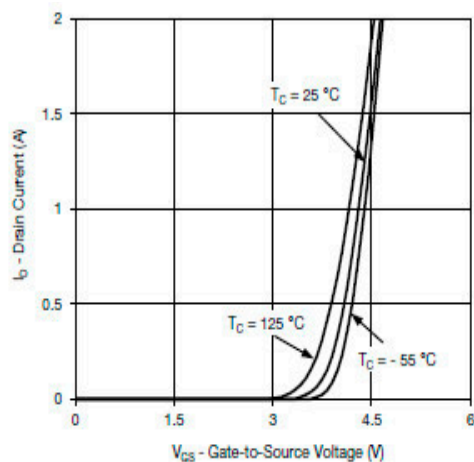
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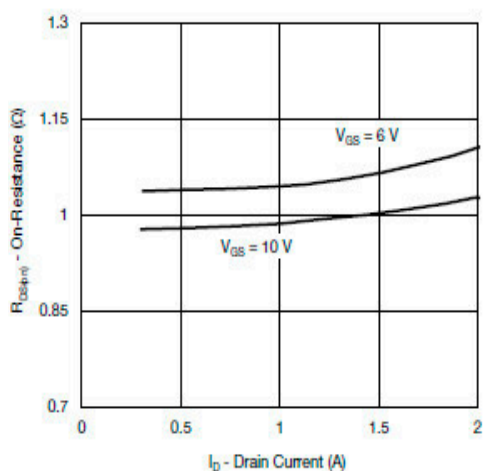
标准特性和热特性曲线



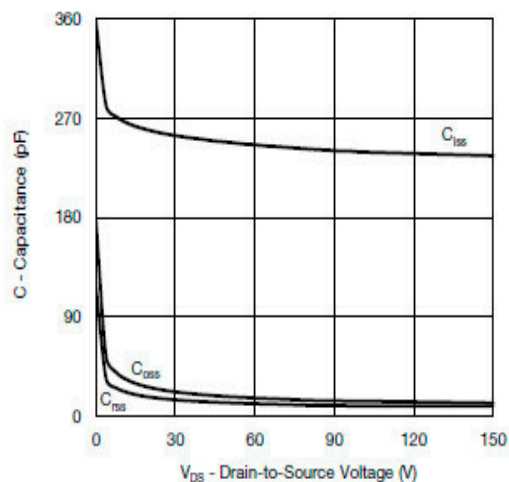
Output Characteristics



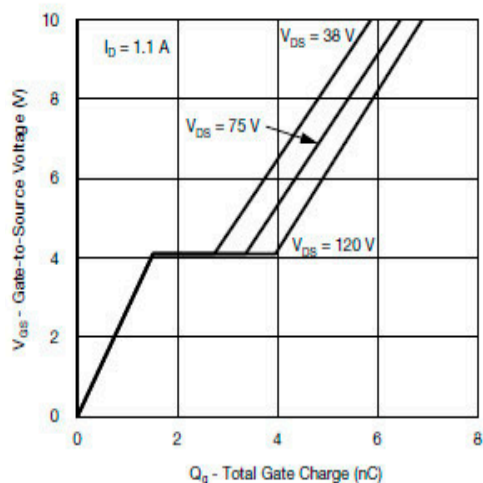
Transfer Characteristics



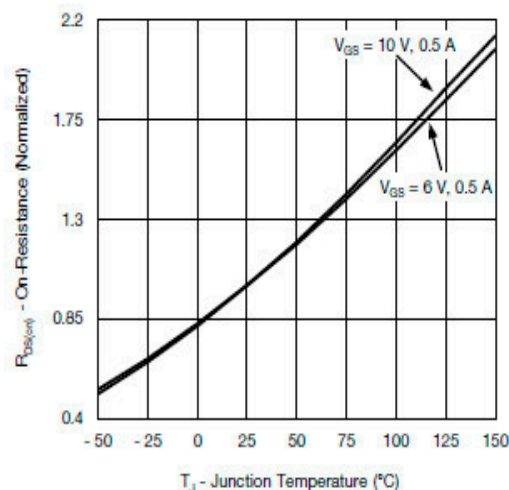
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge

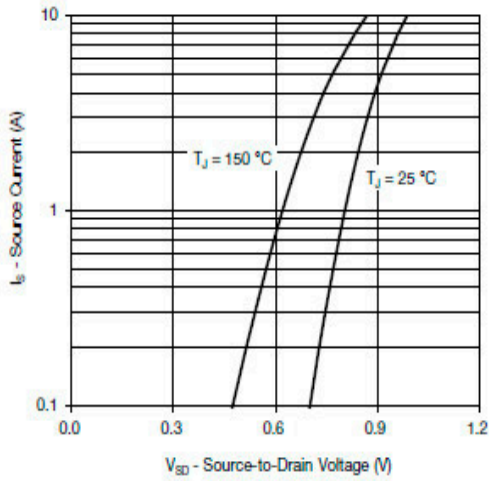


On-Resistance vs. Junction Temperature

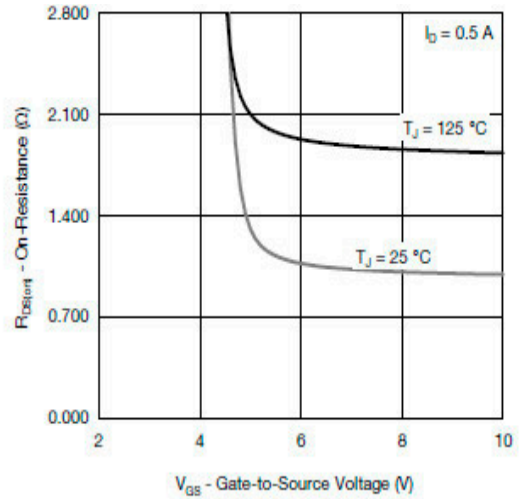
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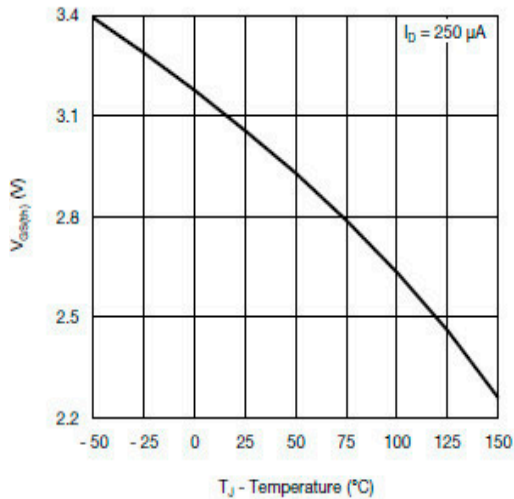
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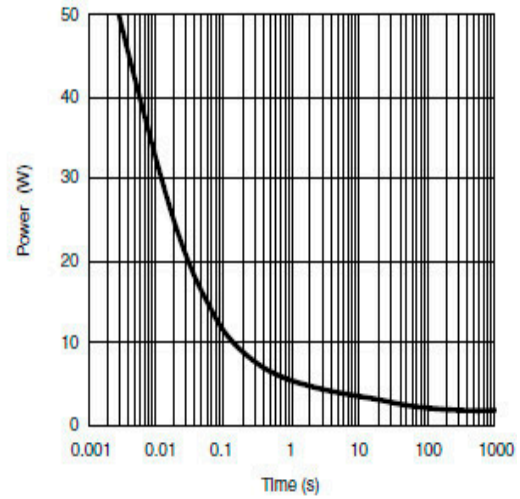
Source-Drain Diode Forward Voltage



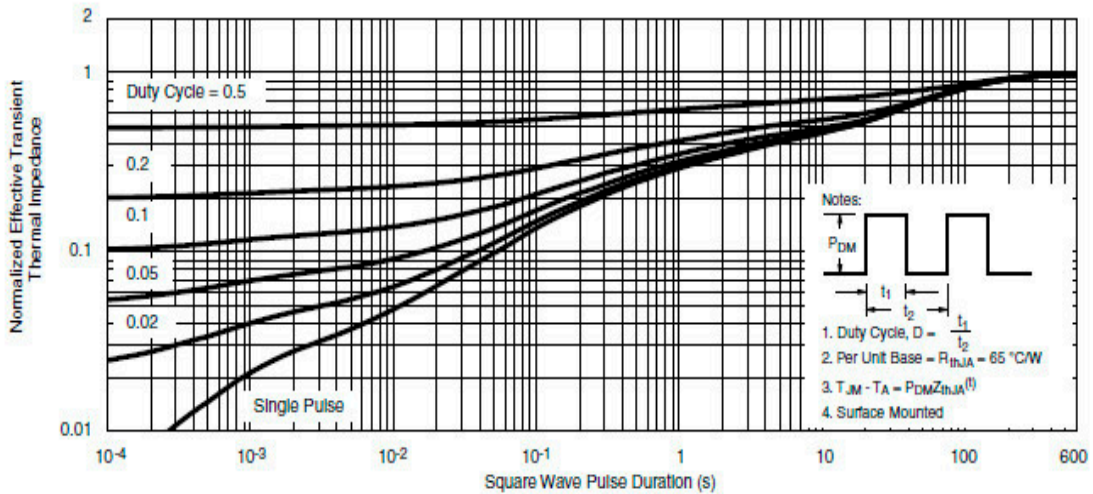
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

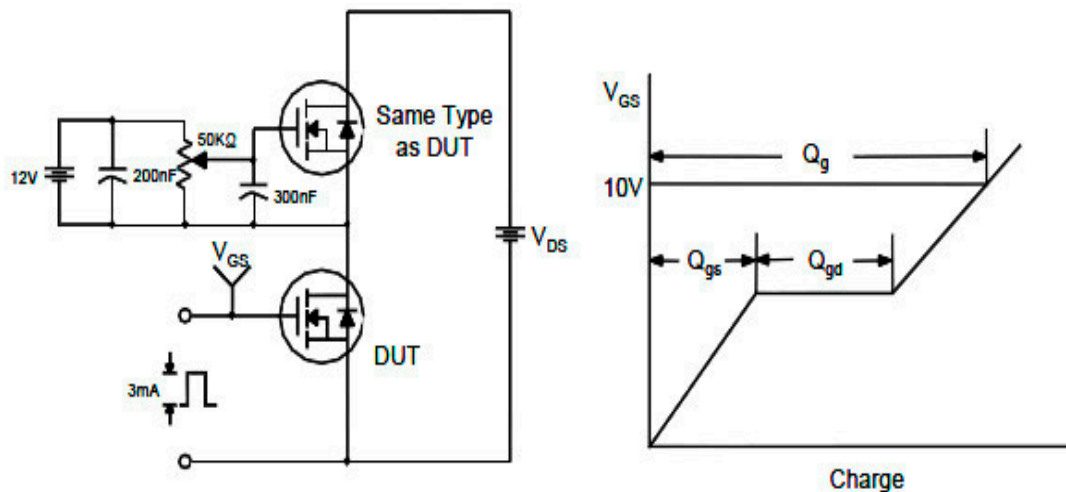
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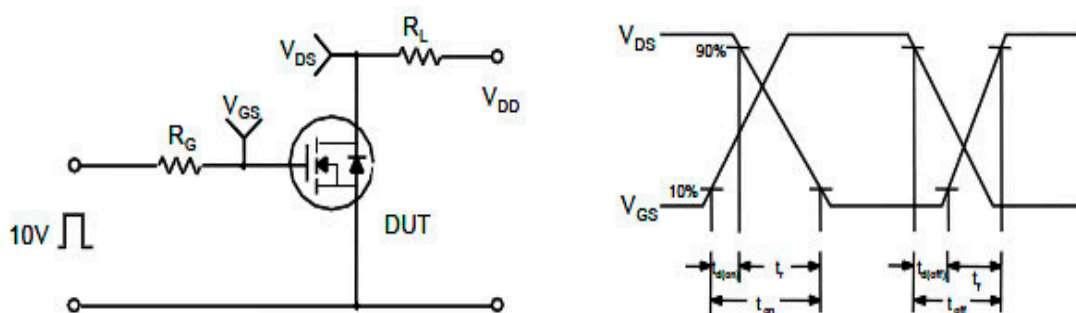
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■ 测试电路和波形

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

